Nicolas Grandjean

List of Publications by Year
in descending order

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559 papers	17,787 citations	17776 65 h-index	31191 106 g-index
566 all docs	566 docs citations	566 times ranked	9723 citing authors

#	Article	IF	Citations
1	Defects in III-N LEDs: experimental identification and impact on electro-optical characteristics. , 2022, , .		0
2	Deep defects in InGaN LEDs: modeling the impact on the electrical characteristics. , 2022, , .		0
3	Near ultraviolet photonic integrated lasers based on silicon nitride. APL Photonics, 2022, 7, .	3.0	25
4	Single photon emission and recombination dynamics in self-assembled GaN/AlN quantum dots. Light: Science and Applications, 2022, 11, 114.	7.7	19
5	Dark-level trapping, lateral confinement, and built-in electric field contributions to the carrier dynamics in c-plane GaN/AlN quantum dots emitting in the UV range. Journal of Applied Physics, 2021, 129, .	1.1	6
6	Smooth GaN membranes by polarization-assisted electrochemical etching. Applied Physics Letters, 2021, 118, .	1.5	8
7	GaN buffer growth temperature and efficiency of InGaN/GaN quantum wells: The critical role of nitrogen vacancies at the GaN surface. Applied Physics Letters, 2021, 118, .	1.5	17
8	High conductivity InAlN/GaN multi-channel two-dimensional electron gases. Semiconductor Science and Technology, 2021, 36, 055020.	1.0	4
9	Imaging Nonradiative Point Defects Buried in Quantum Wells Using Cathodoluminescence. Nano Letters, 2021, 21, 5217-5224.	4.5	20
10	Ultrafast-nonlinear ultraviolet pulse modulation in an AlInGaN polariton waveguide operating up to room temperature. Nature Communications, 2021, 12, 3504.	5.8	15
11	Modeling the electrical characteristics of InGaN/GaN LED structures based on experimentally-measured defect characteristics. Journal Physics D: Applied Physics, 2021, 54, 425105.	1.3	21
12	Effects of quantum-well indium content on deep defects and reliability of InGaN/GaN light-emitting diodes with under layer. Journal Physics D: Applied Physics, 2021, 54, 505108.	1.3	11
13	Defect incorporation in In-containing layers and quantum wells: experimental analysis via deep level profiling and optical spectroscopy. Journal Physics D: Applied Physics, 2021, 54, 025108.	1.3	20
14	Broadened Bandwidth Amplified Spontaneous Emission from Blue GaN-Based Short-Cavity Superluminescent Light-Emitting Diodes. ECS Journal of Solid State Science and Technology, 2020, 9, 015019.	0.9	5
15	Polariton relaxation and polariton nonlinearities in nonresonantly cw-pumped III-nitride slab waveguides. Physical Review B, 2020, 102, .	1.1	5
16	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. Journal Physics D: Applied Physics, 2020, 53, 445111.	1.3	4
17	Interplay of intrinsic and extrinsic states in pinning and passivation of m-plane facets of GaN n-p-n junctions. Journal of Applied Physics, 2020, 128, .	1.1	2
18	Toward Bright and Pure Single Photon Emitters at 300 K Based on GaN Quantum Dots on Silicon. ACS Photonics, 2020, 7, 1515-1522.	3.2	36

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19	Impact of defects on Auger recombination in c-plane InGaN/GaN single quantum well in the efficiency droop regime. Applied Physics Letters, 2020, 116, .	1.5	14
20	Deep traps in InGaN/GaN single quantum well structures grown with and without InGaN underlayers. Journal of Alloys and Compounds, 2020, 845, 156269.	2.8	4
21	III-nitride photonic cavities. Nanophotonics, 2020, 9, 569-598.	2.9	21
22	Doubly resonant second-harmonic generation of a vortex beam from a bound state in the continuum. Optica, 2020, 7, 1126.	4.8	44
23	Interplay of anomalous strain relaxation and minimization of polarization changes at nitride semiconductor heterointerfaces. Physical Review B, 2020, 102, .	1.1	3
24	Doubly Resonant Second Harmonic Generation in Photonic Crystal Cavities via Bound States in the Continuum. , 2020, , .		0
25	Efficient second harmonic generation in a doubly resonant photonic crystal cavity based on a bound state in the continuum. , 2020, , .		0
26	Probing Alloy Formation Using Different Excitonic Species: The Particular Case of InGaN. Physical Review X, 2019, 9, .	2.8	4
27	Short cavity InGaN-based laser diodes with cavity length below 300 Î¼m. Semiconductor Science and Technology, 2019, 34, 085005.	1.0	12
28	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. Journal of Applied Physics, 2019, 126, .	1.1	21
29	InAlN underlayer for near ultraviolet InGaN based light emitting diodes. Applied Physics Express, 2019, 12, 034002.	1.1	32
30	Density control of GaN quantum dots on AlN single crystal. Applied Physics Letters, 2019, 114, .	1.5	20
31	Narrow Linewidth InGaN Laser Diodes Based on External Cavity Fiber Bragg Grating. , 2019, , .		0
32	Low-temperature growth of n ⁺⁺-GaN by metalorganic chemical vapor deposition to achieve low-resistivity tunnel junctions on blue light emitting diodes. Semiconductor Science and Technology, 2019, 34, 015002.	1.0	9
33	Impact of Mode-Hopping Noise on InGaN Edge Emitting Laser Relative Intensity Noise Properties. IEEE Journal of Quantum Electronics, 2018, 54, 1-7.	1.0	7
34	A quantum optical study of thresholdless lasing features in high-Î² nitride nanobeam cavities. Nature Communications, 2018, 9, 564.	5.8	50
35	Optical absorption edge broadening in thick InGaN layers: Random alloy atomic disorder and growth mode induced fluctuations. Applied Physics Letters, 2018, 112, .	1.5	31
36	Impact of surface morphology on the properties of light emission in InGaN epilayers. Applied Physics Express, 2018, 11, 051004.	1.1	9

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37	Optical absorption and oxygen passivation of surface states in III-nitride photonic devices. Journal of Applied Physics, 2018, 123, .	1.1	23
38	GaN surface as the source of non-radiative defects in InGaN/GaN quantum wells. Applied Physics Letters, 2018, 113, .	1.5	93
39	Alloy disorder limited mobility of InGaN two-dimensional electron gas. Applied Physics Letters, 2018, 112, .	1.5	23
40	Composition Metrology of Ternary Semiconductor Alloys Analyzed by Atom Probe Tomography. Journal of Physical Chemistry C, 2018, 122, 16704-16714.	1.5	22
41	Near-UV narrow bandwidth optical gain in lattice-matched IIIâ€“nitride waveguides. Japanese Journal of Applied Physics, 2018, 57, 090305.	0.8	3
42	Excited states of neutral donor bound excitons in GaN. Journal of Applied Physics, 2018, 123, .	1.1	7
43	In distribution in InGaN quantum wells: influence of phase separation, In segregation and In desorption. , 2018, , 285-288.		0
44	Fermi-level pinning and intrinsic surface states of Al1â^'xInxN(101Â¯) surfaces. Applied Physics Letters, 2017, 110, .	1.5	5
45	Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. Nano Letters, 2017, 17, 3347-3355.	4.5	9
46	Multilayer porous structures on GaN for the fabrication of Bragg reflectors. Proceedings of SPIE, 2017, , .	0.8	4
47	Efficient continuous-wave nonlinear frequency conversion in high-Q gallium nitride photonic crystal cavities on silicon. APL Photonics, 2017, 2, .	3.0	38
48	Enhancement of Auger recombination induced by carrier localization in InGaN/GaN quantum wells. Physical Review B, 2017, 95, .	1.1	41
49	Propagating Polaritons in III-Nitride Slab Waveguides. Physical Review Applied, 2017, 7, .	1.5	32
50	Multilayer porous structures of HVPE and MOCVD grown GaN for photonic applications. Superlattices and Microstructures, 2017, 102, 221-234.	1.4	17
51	Quantification of scattering loss of III-nitride photonic crystal cavities in the blue spectral range. Physical Review B, 2017, 95, .	1.1	14
52	AlN grown on Si(1 1 1) by ammonia-molecular beam epitaxy in the 900â€“1200 Â°C temperature range. Journal of Crystal Growth, 2017, 476, 58-63.	0.7	41
53	Determining the nature of excitonic dephasing in high-quality GaN/AlGaN quantum wells through time-resolved and spectrally resolved four-wave mixing spectroscopy. Physical Review B, 2017, 96, .	1.1	7
54	Critical thickness of GaN on AlN: impact of growth temperature and dislocation density. Semiconductor Science and Technology, 2017, 32, 075010.	1.0	33

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55	Burying non-radiative defects in InGaN underlayer to increase InGaN/GaN quantum well efficiency. Applied Physics Letters, 2017, 111, .	1.5	99
56	Efficient harmonic generation in high-Q gallium nitride photonic crystal cavities on silicon. , 2017, , .		0
57	Light-emitting diode technology and applications: introduction. Photonics Research, 2017, 5, LED1.	3.4	5
58	Vacuum-field Rabi Splitting at SWIR in Photocurrent of Quantum Cascade Infrared Photodetectors Coupled to Metamaterial Nano-antennas. , 2017, , .		0
59	<inline-formula> <tex-math notation="LaTeX">W </tex-math> </inline-formula>-Band MMIC Amplifiers Based on AlInN/GaN HEMTs Grown on Silicon. IEEE Electron Device Letters, 2016, 37, 1025-1028.	2.2	14
60	Selective heteroepitaxy on deeply grooved substrate: A route to low cost semipolar GaN platforms of bulk quality. Applied Physics Letters, 2016, 109, 082101.	1.5	8
61	GaN superluminescent diodes and their applications. , 2016, , .		3
62	High p-type GaN for advanced optoelectronic devices. , 2016, , .		1
63	Far-field coupling in nanobeam photonic crystal cavities. Applied Physics Letters, 2016, 108, .	1.5	5
64	Photocapacitance spectroscopy of InAlN nearly lattice-matched to GaN. Applied Physics Letters, 2016, 109, .	1.5	4
65	Assessing the Composition of Wide Bandgap Compound Semiconductors by Atom Probe Tomography: A Metrological Problem. Microscopy and Microanalysis, 2016, 22, 650-651.	0.2	1
66	Strain and compositional fluctuations in Al0.81In0.19N/GaN heterostructures. Applied Physics Letters, 2016, 109, 132102.	1.5	4
67	Backward diodes using heavily Mg-doped GaN growth by ammonia molecular-beam epitaxy. Applied Physics Letters, 2016, 108, .	1.5	26
68	Exciton dynamics at a single dislocation in GaN probed by picosecond time-resolved cathodoluminescence. Applied Physics Letters, 2016, 109, .	1.5	49
69	Statistical correction of atom probe tomography data of semiconductor alloys combined with optical spectroscopy: The case of Al0.25Ga0.75N. Journal of Applied Physics, 2016, 119, .	1.1	49
70	Optical properties of nearly lattice-matched GaN/(Al,In)N quantum wells. Journal of Applied Physics, 2016, 119, 205708.	1.1	1
71	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. Journal of Applied Physics, 2016, 119, 245702.	1.1	9
72	Low p-type contact resistance by field-emission tunneling in highly Mg-doped GaN. Applied Physics Letters, 2016, 109, .	1.5	11

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73	Calcium impurity as a source of non-radiative recombination in (In,Ga)N layers grown by molecular beam epitaxy. Applied Physics Letters, 2016, 109, .	1.5	23
74	Quantification of roughness and spatial distribution of dislocations in MBE and MOVPE grown LED heterostructures. Materials Science in Semiconductor Processing, 2016, 55, 12-18.	1.9	3
75	InGaN laser diode with metal-free laser ridge using n⁺-GaN contact layers. Applied Physics Express, 2016, 9, 061004.	1.1	29
76	Statistical nanoscale study of localised radiative transitions in GaN/AlGaN quantum wells and AlGaN epitaxial layers. Semiconductor Science and Technology, 2016, 31, 095009.	1.0	22
77	Room-Temperature Transport of Indirect Excitons in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo stretchy="false">(</mml:mo><mml:mi>Al</mml:mi><mml:mo>,</mml:mo><mml:mi>Ga</mml:mi><mml:mo) Tj ETQq1 1 0.784314 rgBT mathvariant="normal">N</mml:mi><mml:mo>/</mml:mo><mml:mi>GaN</mml:mi></mml:mrow></mml:math>Quantum Wells. Physical Review Applied, 2016, 6, .	1.5	26
78	Carrier-density-dependent recombination dynamics of excitons and electron-hole plasma in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>m</mml:mi></mml:math> -plane InGaN/GaN quantum wells. Physical Review B, 2016, 94, .	1.1	41
79	Technology of integrated self-aligned E/D-mode n⁺⁺GaN/InAlN/AlN/GaN MOS HEMTs for mixed-signal electronics. Semiconductor Science and Technology, 2016, 31, 065011.	1.0	12
80	GaN-based superluminescent diodes with long lifetime. Proceedings of SPIE, 2016, , .	0.8	6
81	Critical impact of Ehrlichâ€"SchwÃ¶bel barrier on GaN surface morphology during homoepitaxial growth. Journal of Crystal Growth, 2016, 433, 36-42.	0.7	61
82	Fabrication defects and grating couplers in III-nitride photonic crystal nanobeam lasers (Conference) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5		0
83	Transport of dipolar excitons in (Al,Ga)N/GaN quantum wells. Physical Review B, 2015, 91, .	1.1	23
84	Vectorial near-field imaging of a GaN based photonic crystal cavity. Applied Physics Letters, 2015, 107, .	1.5	7
85	GaN L3 Photonic Crystal Cavities With an Average Quality Factor in Excess of 16000 in the Near Infrared. , 2015, , .		1
86	InGaN laser diodes emitting at 500 nm with p-layers grown by molecular beam epitaxy. Applied Physics Express, 2015, 8, 022105.	1.1	7
87	Solitary pulse-on-demand production by optical injection locking of passively Q-switched InGaN diode laser near lasing threshold. Applied Physics Letters, 2015, 106, .	1.5	4
88	Selfâ€aligned normallyâ€off metalâ€"oxideâ€"semiconductor n⁺⁺GaN/InAlN/GaN high electron mobility transistors. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1086-1090.	0.8	23
89	94-GHz Large-Signal Operation of AlInN/GaN High-Electron-Mobility Transistors on Silicon With Regrown Ohmic Contacts. IEEE Electron Device Letters, 2015, 36, 17-19.	2.2	58
90	Continuous Wave Blue Lasing in III-Nitride Nanobeam Cavity on Silicon. Nano Letters, 2015, 15, 1259-1263.	4.5	51

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91	Cavity-enhanced optical Hall effect in two-dimensional free charge carrier gases detected at terahertz frequencies. Optics Letters, 2015, 40, 2688.	1.7	19
92	Capacitance behavior of InAlN Schottky diodes in presence of large concentrations of shallow and deep states related to oxygen. Journal of Applied Physics, 2015, 117, 185701.	1.1	10
93	InGaN based micro light emitting diodes featuring a buried GaN tunnel junction. Applied Physics Letters, 2015, 107, .	1.5	81
94	Room Temperature Continuous Wave Blue Lasing in High Quality Factor III-Nitride Nanobeam Cavity on Silicon. , 2015, , .		0
95	Low temperature p-type doping of (Al)GaN layers using ammonia molecular beam epitaxy for InGaN laser diodes. Applied Physics Letters, 2014, 105, 241103.	1.5	17
96	n+-GaN grown by ammonia molecular beam epitaxy: Application to regrown contacts. Applied Physics Letters, 2014, 105, .	1.5	21
97	Solitary Pulse-on-Demand Production by Optical Injection Locking of Passively Q-Switched InGaN Diode Lasers Near Lasing Threshold. , 2014, , .		0
98	First demonstration of plasmonic GaN quantum cascade detectors with enhanced efficiency at normal incidence. Optics Express, 2014, 22, 21069.	1.7	14
99	Analysis of structurally sensitive loss in GaN-based VCSEL cavities and its effect on modal discrimination. Optics Express, 2014, 22, 411.	1.7	34
100	Interaction between meta-materials and shallow donors in bulk GaN at THz frequency. Optics Express, 2014, 22, 3199.	1.7	1
101	Shallow donor and deep DX-like center in InAlN layers nearly lattice-matched to GaN. Physical Review B, 2014, 90, .	1.1	14
102	High-temperature Mott transition in wide-band-gap semiconductor quantum wells. Physical Review B, 2014, 90, .	1.1	43
103	Triggering of guiding and antiguiding effects in GaN-based VCSELs. , 2014, , .		1
104	Gallium nitride L3 photonic crystal cavities with an average quality factor of 16â€‰900 in the near infrared. Applied Physics Letters, 2014, 105, .	1.5	28
105	Leakage mechanisms in InAlN based heterostructures. Journal of Applied Physics, 2014, 115, .	1.1	30
106	M-Plane GaN/InAlN Multiple Quantum Wells in Coreâ€“Shell Wire Structure for UV Emission. ACS Photonics, 2014, 1, 38-46.	3.2	42
107	Biexcitonic molecules survive excitons at the Mott transition. Nature Communications, 2014, 5, 5251.	5.8	14
108	Composition of Wide Bandgap Semiconductor Materials and Nanostructures Measured by Atom Probe Tomography and Its Dependence on the Surface Electric Field. Journal of Physical Chemistry C, 2014, 118, 24136-24151.	1.5	135

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109	Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. Applied Physics Letters, 2014, 105, 032101.	1.5	30
110	InGaN/GaN quantum wells for polariton laser diodes: Role of inhomogeneous broadening. Journal of Applied Physics, 2014, 115, .	1.1	15
111	Hot-Electron-Related Degradation in InAlN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2014, 61, 2793-2801.	1.6	37
112	Thermal stability and in situ SiN passivation of InAlN/GaN high electron mobility heterostructures. Applied Physics Letters, 2014, 105, .	1.5	12
113	Ultrathin Body InAlN/GaN HEMTs for High-Temperature (600$^{circ} {m C}$) Electronics. IEEE Electron Device Letters, 2013, 34, 496-498.	2.2	28
114	Optical, structural, and morphological characterisation of epitaxial ZnO films grown by pulsed-laser deposition. Thin Solid Films, 2013, 539, 55-59.	0.8	26
115	AlInN-Based HEMTs for Large-Signal Operation at 40 GHz. IEEE Transactions on Electron Devices, 2013, 60, 3091-3098.	1.6	29
116	Impact of saturation on the polariton renormalization in III-nitride based planar microcavities. Physical Review B, 2013, 88, .	1.1	17
117	Engineering the Lateral Optical Guiding in Gallium Nitride-Based Vertical-Cavity Surface-Emitting Laser Cavities to Reach the Lowest Threshold Gain. Japanese Journal of Applied Physics, 2013, 52, 08JG04.	0.8	35
118	Hybrid and Passive Mode-Locking of a Monolithic Two-Section MQW InGaN/GaN Laser Diode. IEEE Photonics Technology Letters, 2013, 25, 1514-1516.	1.3	8
119	Large-kexciton dynamics in GaN epilayers: Nonthermal and thermal regimes. Physical Review B, 2013, 87, .	1.1	9
120	Intrinsic degradation mechanism of nearly lattice-matched InAlN layers grown on GaN substrates. Journal of Applied Physics, 2013, 113, 063506.	1.1	55
121	Peculiarities in the pressure dependence of photoluminescence in InAlN. Physica Status Solidi (B): Basic Research, 2013, 250, 677-682.	0.7	3
122	Schottky-barrier normally off GaN/InAlN/AlN/GaN HEMT with selectively etched access region. IEEE Electron Device Letters, 2013, 34, 432-434.	2.2	33
123	Q-factor of (In,Ga)N containing III-nitride microcavity grown by multiple deposition techniques. Journal of Applied Physics, 2013, 114, .	1.1	11
124	ZrO2/InAlN/GaN Metalâ€“Oxideâ€“Semiconductor Heterostructure Field-Effect Transistors with InAlN Barrier of Different Compositions. Japanese Journal of Applied Physics, 2013, 52, 08JN07.	0.8	5
125	GaN-on-insulator technology for high-temperature electronics beyond 400 Â°C. Semiconductor Science and Technology, 2013, 28, 074026.	1.0	16
126	In-depth analysis of injection-seeded long external cavity InGaN/GaN surface-emitting laser. Journal of Applied Physics, 2013, 113, .	1.1	4

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127	AlN-Capped AlInN/GaN High Electron Mobility Transistors with 4.5 W/mm Output Power at 40 GHz. Japanese Journal of Applied Physics, 2013, 52, 08JN16.	0.8	7
128	Mode locking in monolithic two-section InGaN blue-violet semiconductor lasers. Applied Physics Letters, 2013, 102, .	1.5	13
129	Ultrathin InAlN/GaN heterostructures on sapphire for high on/off current ratio high electron mobility transistors. Journal of Applied Physics, 2013, 113, 214503.	1.1	17
130	Integrated photonics on silicon with wide bandgap GaN semiconductor. Applied Physics Letters, 2013, 102, .	1.5	56
131	Defect states characterization of non-annealed and annealed ZrO2/InAlN/GaN structures by capacitance measurements. Applied Physics Letters, 2013, 102, .	1.5	8
132	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown ona-Plane GaN Substrates. Japanese Journal of Applied Physics, 2013, 52, 08JC01.	0.8	8
133	Properties of InAlN layers nearly lattice-matched to GaN and their use for photonics and electronics. , 2013, , 177-226.		4
134	Growth of Thick GaN Layers by Hydride Vapor Phase Epitaxy on Sapphire Substrate with Internally Focused Laser Processing. Applied Physics Express, 2013, 6, 035502.	1.1	11
135	Toward Quantum Fluids at Room Temperature: Polariton Condensation in III-Nitride Based Microcavities. Springer Series in Solid-state Sciences, 2013, , 201-230.	0.3	0
136	Polariton Lasing at Room Temperature. , 2013, , .		0
137	Superluminescent light emitting diodes: the best out of two worlds. Proceedings of SPIE, 2012, , .	0.8	18
138	Near-infrared characterization of gallium nitride photonic-crystal waveguides and cavities. Optics Letters, 2012, 37, 4588.	1.7	25
139	Optically pumped long external cavity InGaN/GaN surface-emitting laser with injection seeding from a planar microcavity. Applied Physics Letters, 2012, 101, .	1.5	8
140	Nonlinear emission properties of an optically anisotropic GaN-based microcavity. Physical Review B, 2012, 86, .	1.1	5
141	On the origin of basal stacking faults in nonpolar wurtzite films epitaxially grown on sapphire substrates. Journal of Applied Physics, 2012, 112, .	1.1	25
142	Impact of biexcitons on the relaxation mechanisms of polaritons in III-nitride based multiple quantum well microcavities. Physical Review B, 2012, 85, .	1.1	13
143	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. Japanese Journal of Applied Physics, 2012, 51, 054102.	0.8	2
144	Static and dynamic properties of multi-section InGaN-based laser diodes. Journal of Applied Physics, 2012, 112, .	1.1	12

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145	Measurement of polarization-induced electric fields in GaN/AlInN quantum wells. Applied Physics Letters, 2012, 101, .	1.5	9
146	Polariton lasers. , 2012, , .		0
147	Early stage degradation of InAlN/GaN HEMTs during electrical stress. , 2012, , .		1
148	High quality factor two dimensional GaN photonic crystal cavity membranes grown on silicon substrate. Applied Physics Letters, 2012, 100, .	1.5	64
149	InAlN/GaN HEMTs for Operation in the 1000 $^{circ} hbox{C}$ Regime: A First Experiment. IEEE Electron Device Letters, 2012, 33, 985-987.	2.2	82
150	Generic picture of the emission properties of III-nitride polariton laser diodes: Steady state and current modulation response. Physical Review B, 2012, 86, .	1.1	25
151	Thermal annealing of molecular beam epitaxy-grown InGaN/GaN single quantum well. Semiconductor Science and Technology, 2012, 27, 105023.	1.0	14
152	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. Journal of Applied Physics, 2012, 111, 033517.	1.1	10
153	Mg doping for p-type AlInN lattice-matched to GaN. Applied Physics Letters, 2012, 101, 082113.	1.5	39
154	III-nitride intersubband photonics. Proceedings of SPIE, 2012, , .	0.8	0
155	Blue monolithic AlInN-based vertical cavity surface emitting laser diode on free-standing GaN substrate. Applied Physics Letters, 2012, 101, .	1.5	138
156	A simplified GaN/AlGaN quantum cascade detector with an alloy extractor. Applied Physics Letters, 2012, 101, .	1.5	28
157	Two-color GaN/AlGaN quantum cascade detector at short infrared wavelengths of 1 and 1.7â€‰Î¼m. Applied Physics Letters, 2012, 100, .	1.5	52
158	Low loss EEL spectroscopy performed on In_xAl_{1â€x}N layers grown by MOVPE: comparison between experiment and abâ€initio calculations. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 989-992.	0.8	2
159	Investigation of InGaN/GaN quantum wells for polariton laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1325-1329.	0.8	8
160	GaN on sapphire mesa technology. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 945-948.	0.8	5
161	Explanation of threshold voltage scaling in enhancement-mode InAlN/AlNâ€“GaN metal oxide semiconductor high electron mobility transistors on Si substrates. Thin Solid Films, 2012, 520, 6230-6232.	0.8	16
162	Advantages and remaining issues of state-of-the-artm-plane freestanding GaN substrates grown by halide vapor phase epitaxy form-plane InGaN epitaxial growth. Semiconductor Science and Technology, 2012, 27, 024008.	1.0	15

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163	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. Japanese Journal of Applied Physics, 2012, 51, 054102.	0.8	13
164	A novel class of coherent light emitters: polariton lasers. Semiconductor Science and Technology, 2011, 26, 014030.	1.0	24
165	Electrical properties of InAlN/GaN high electron mobility transistor with Al2O3, ZrO2, and GdScO3 gate dielectrics. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	30
166	Self heating in AlInN/AlN/GaN high power devices: Origin and impact on contact breakdown and IV characteristics. Journal of Applied Physics, 2011, 109, .	1.1	25
167	One-dimensional exciton luminescence induced by extended defects in nonpolar GaN/(Al,Ga)N quantum wells. Semiconductor Science and Technology, 2011, 26, 025012.	1.0	15
168	Recombination coefficients of GaN-based laser diodes. Journal of Applied Physics, 2011, 109, .	1.1	77
169	Fully Passivated AlInN/GaN HEMTs With $f_{m T}/f_{m MAX}$ of 205/220 GHz. IEEE Electron Device Letters, 2011, 32, 1364-1366.	2.2	72
170	Diamond overgrown InAlN/GaN HEMT. Diamond and Related Materials, 2011, 20, 604-608.	1.8	56
171	Effects of the annealing temperature on the structural and electronic properties of MBE grown InGaN/GaN quantum wells. Journal of Physics: Conference Series, 2011, 326, 012012.	0.3	1
172	TEM and XANES study of MOVPE grown InAlN layers with different indium content. Journal of Physics: Conference Series, 2011, 326, 012013.	0.3	10
173	Improvements of High Performance 2-nm-thin InAlNâˆ•AlN Barrier Devices by Interface Engineering. , 2011, , .		0
174	Solid-state lighting on glass. Nature Photonics, 2011, 5, 714-715.	15.6	7
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